

LET16045C

RF power transistor from the LdmoST family of n-channel enhancement-mode lateral MOSFETs

Features

- Excellent thermal stability
- Common source configuration
- P_{OUT} (@28 V) = 45 W with 16 dB gain @ 1600 MHz
- BeO free package
- In compliance with the 2002/95/EC European directive

Description

The LET16045C is a common source N-channel enhancement-mode lateral field-effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.6 GHz. The LET16045C is designed for high gain and broadband performance operating in common source mode at 28 V. It is ideal for INMARSAT satellite communications.

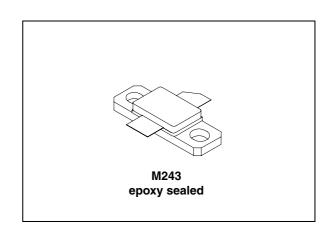


Figure 1. Pin out

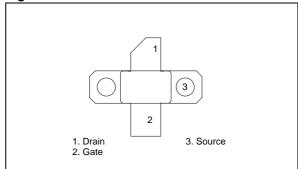


Table 1. Device summary

Order code	Package	Branding
LET16045C	M243	LET16045C

Maximum ratings LET16045C

1 Maximum ratings

Table 2. Absolute maximum ratings ($T_{CASE} = 25 \,^{\circ}C$)

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-source voltage	80	V
V_{GS}	Gate-source voltage	-0.5 to +15	V
I _D	Drain current	9	Α
P _{DISS}	Power dissipation (@ T _C = 70 °C)	100	W
TJ	Max. operating junction temperature	200	°C
T _{STG}	Storage temperature	-65 to +150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{th(JC)}	Junction-case thermal resistance	1.3	°C/W

2 Electrical characteristics

T_C = 25 °C

Table 4. Static

Symbol	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	$V_{GS} = 0 \text{ V}; I_{DS} = 10 \text{ mA}$	80			V
I _{DSS}	V _{GS} = 0 V; V _{DS} = 28 V			1	μА
I _{GSS}	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}$			1	μΑ
V _{GS(Q)}	V _{DS} = 28 V; I _D = 300 mA	2.0		5.0	V
V _{DS(ON)}	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}$			1.1	V
G _{FS}	$V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}$	2.5			mho
C _{ISS}	V _{GS} = 0 V; V _{DS} = 28 V; f = 1 MHz		58		pF
C _{OSS}	V _{GS} = 0 V; V _{DS} = 28 V; f = 1 MHz		29		pF
C _{RSS}	V _{GS} = 0 V; V _{DS} = 28 V; f = 1 MHz		0.8		pF

Table 5. Dynamic

Symbol	Test conditions	Min.	Тур.	Max.	Unit
P _{OUT}	$V_{DD} = 28 \text{ V}; I_{DQ} = 400 \text{ mA}; P_{IN} = 2 \text{ W}$	45	54		W
G _{PS}	V _{DD} = 28 V; I _{DQ} = 400 mA; P _{OUT} = 45 W	15	16		dB
h _D	$V_{DD} = 28 \text{ V}; I_{DQ} = 400 \text{ mA}; P_{OUT} = 45 \text{ W}$		55	-	%
Load mismatch	V_{DD} = 28 V; I_{DQ} = 400 mA; P_{OUT} = 50 W; f = 1600 MHz All phase angles		20:1		VSWR

Table 6. Impedance data

Frequency (MHz)	Z source (Ω)	Z load (Ω)
1600	1.1 - j1.6	1.1 - j0.6

3 Typical performances

Figure 2. Gain and efficiency vs output power

80 24 Efficiency 70 22 20 **Gain (dB)** 16 14 50 % 40 02 Efficiency (%) Freq = 1600 MHz $V_{DD} = 28V$ $I_{DQ} = 400 \text{ mA}$ 12 20 10 10 0 10 20 30 40 50 60

Output Power (W)

Figure 3. Gain vs ouptut power and bias current

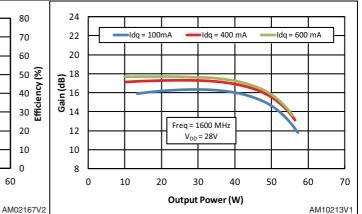
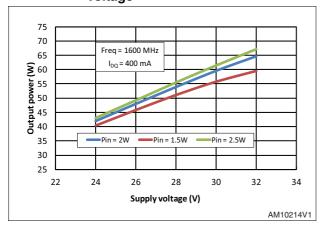


Figure 4. Ouptut power vs drain supply voltage



4 Package mechanical data

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Dim.	mm			inch		
	Min.	Тур	Max.	Min.	Тур	Max.
Α	5.21		5.72	0.205		0.225
В	5.46		6.48	0.215		0.255
С	5.59		6.1	0.22		0.24
D		14.27			0.562	
E	20.07		20.57	0.79		0.81
F	8.89		9.4	0.35		0.37
G	0.1		0.15	0.004		0.006
Н	3.18		4.45	0.125		0.175

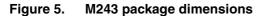
2.24

1.78

0.072

0.05

Table 7. M243 (.230 x .360 2L N/HERM W/FLG) mechanical data

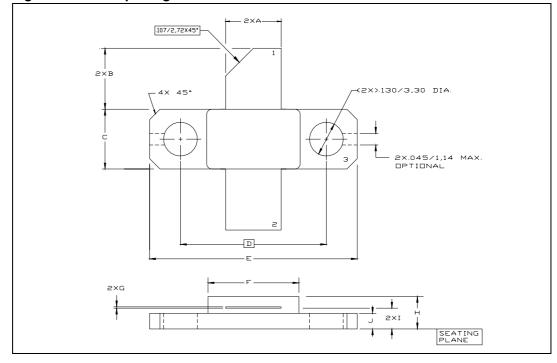


1.83

1.27

Τ

J



0.088

0.07

Revision history LET16045C

5 Revision history

Table 8. Document revision history

Date	Revision	Changes	
14-Sep-2011	1	Initial release.	
04-Nov-2011	2	Updated Table 3: Thermal data, Table 4: Static, Table 5: Dynamic and Figure 3: Gain vs ouptut power and bias current. Inserted Table 6: Impedance data and Figure 2: Gain and efficiency vs output power and Figure 4: Ouptut power vs drain supply voltage.	

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